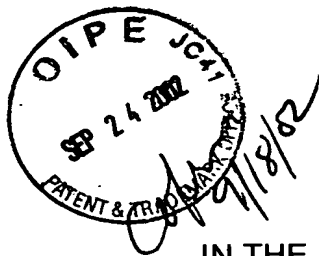


2823



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231 on September 18, 2002

Mary Ann Copas, Secretary

In the Application of Wilfred Lerch et al

Ser.No.: 09/980,754

Filed: February 15, 2002

For: METHOD OF GENERATING DEFECTS IN A LATTICE STRUCTURE OF A SEMI-CONDUCTOR MATERIAL

Art Unit: 2823

Examiner: Julio J. Maldonado

Assistant Commissioner for Patents

Washington, DC 20231

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#11/B

Amend
J. McMillen
9/28/02

AMENDMENT IN RESPONSE TO OFFICE ACTION DATED 06/18/2002

Dear Sir:

In response to the outstanding Office Action, please amend the above-identified application as follows:

IN THE CLAIMS:

Claim 43 has been amended to read as follows:

43. (Once amended) A method according to claim 28, which includes
reducing thermal stressing of a semiconductor wafer.

B